NEC

PNP SILICON POWER TRANSISTOR **2SA1486**

DESCRIPTION

The 2SA1486 is designed for use in high speed and high volt-

age switching.

It is suitable for switching regulators, DC-DC converters and $% \left(\mathbf{r}\right) =\left(\mathbf{r}\right)$

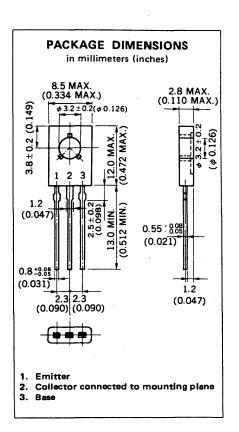
ultrasonic appliance applications.

FEATURES

- High speed switching
- High Voltage

ABSOLUTE MAXIMUM RATINGS

Maximum Tem	peratures						
Storage T	'emperature	5 to +1!	50 °C				
Junction	Temperature 150	°C Maxi	mum				
	er Dissipation (T _C = 25 °C)						
Total Power Dissipation 15							
Maximum Volt	age and Currents (T _a = 25 °C)						
V _{CBO}	Collector to Base Voltage	600	٧				
V _{CEO}	Collector to Emitter Voltage	-600	٧				
V_{EBO}	Emitter to Base Voltage	-7.0	٧				
(C(DC)	Collector Current (DC)	-1.0	Α				
IC(pulse)	Collector Current (Pulse)*	-2.0	Α				
*PW ≤ 300 μs, Duty Cycle ≤ 10 %							



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS	
ton	Turn On Time		0.1	0.5	μs		
t _{stg}	Storage Time		3.5	5.0	μs	$I_C = -0.5 \text{ A}, I_{B1} = -I_{B2} = -0.1 \text{ A}$ $R_L = 500 \Omega, V_{CC} = -250 \text{ V}$	
tf	Fall Time	,	80.0	0.5	μs		
hFE1**	DC Current Gain	30		120	_	$V_{CE} = -5.0 \text{ V, I}_{C} = -0.1 \text{ A}$	
hFE2**	DC Current Gain	5			_	$V_{CE} = -5.0 \text{ V}, I_{C} = -0.5 \text{ A}$	
VCE(sat)**	Collector Saturation Voltage			-1.0	V	$I_C = -0.3 \text{ A}, I_B = -0.06 \text{ A}$	
V _{BE(sat)**}	Base Saturation Voltage			-1.2	V	$I_C = -0.3 \text{ A}, I_B = -0.06 \text{ A}$	
ІСВО	Collector Cutoff Current			-10	μΑ	$V_{CB} = -600 V, I_{E} = 0$	
IEBO	Emitter Cutoff Current			-10	μΑ	V _{EB} = -7.0 V, I _C = 0	

^{**} Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2 %

Classification of hee1

Rank	М	L	κ					
Range	30 to 60	40 to 80	60 to 120					

Test Conditions: VCE = -5.0 V, IC = -0.1 A

TYPICAL CHARACTERISTICS (Ta = 25 °C)

